"Yش / Descriptions

SOT-323 NPN Silicon NPN transistor in a SOT-323 Plastic Package.

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, , , MMBTA92W

High voltage, Low saturation voltage, low collector capacitance output, complementary pair with MMBTA92W.

High voltage control circuit.

Л ف ً ặ ≠ ع / Equivalent Circuit



PIN1 Emitter PIN 2 Base PIN 3 Collector

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Parameter	Symbol	Rating	Unit
Collector to Base Voltage	V_{CBO}	300	V
Collector to Emitter Voltage	V_{CEO}	300	V
Emitter to Base Voltage	V_{EBO}	6.0	V
Collector Current - Continuous	I_C	500	mA
Collector Power Dissipation	P_C*	250	mW
Junction Temperature	T_j	150	
Storage Temperature Range	T_{stg}	-55 150	

*: 4.0*4.0*0.15mm^3 FR-4 PCB
*:Device mounted on FR-4 PCB 4.0*4.0*0.15mm^3

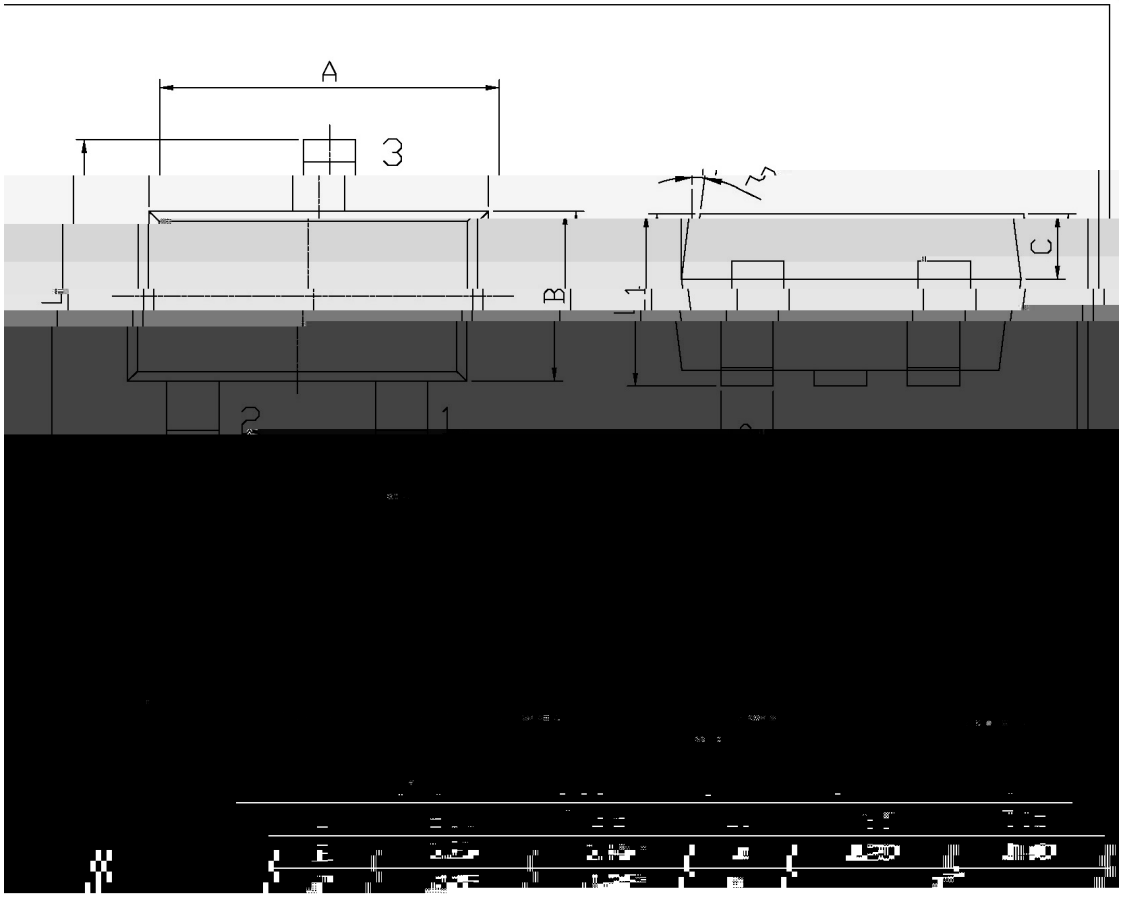
Parameter	Symbol	Test Conditions	Min	Typ	Max	Unit
Collector to Base Breakdown Voltage	V_{CBO}	I_C=100μA I_E=0	300			V
Collector to Emitter Breakdown Voltage	V_{CEO}	I_C=1.0mA I_B=0	300			V
Emitter to Base Breakdown Voltage	V_{EBO}	I_E=100μA I_C=0	6.0			V
Collector Cut-Off Current	I_{CBO}	V_{CB}=200V I_E=0			0.1	μA
Emitter Base Cut-Off Current	I_{EBO}	V_{BE}=6.0V I_C=0			0.1	μA
DC Current Gain	$h_{FE(1)}$	V_{CE}=10V I_C=10mA	40			
	$h_{FE(2)}$	V_{CE}=10V I_C=30mA	40			
	$h_{FE(3)}$	V_{CE}=10V I_C=1.0mA	25			
Collector to Emitter Saturation Voltage	$V_{CE(sat)}$	I_C=20mA I_B=2.0mA			0.5	V
Base to Emitter Saturation Voltage	$V_{BE(sat)}$	I_C=20mA I_B=2.0mA			0.9	V
Transition Frequency	f_T	I_C=10mA				

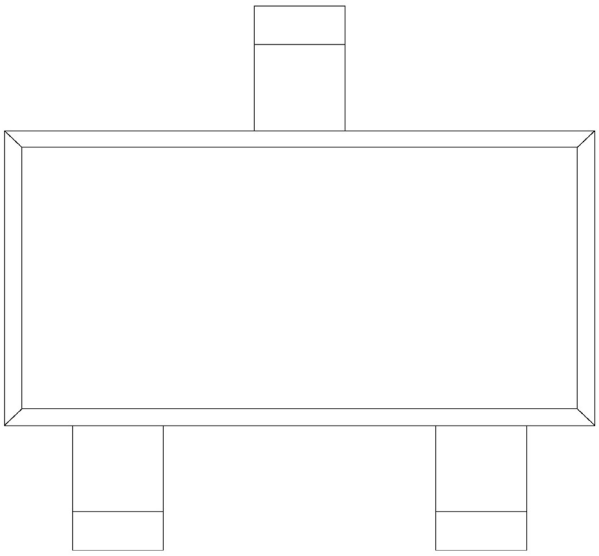
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ᵘ ĖÕĻ ƒ / Package Dimensions

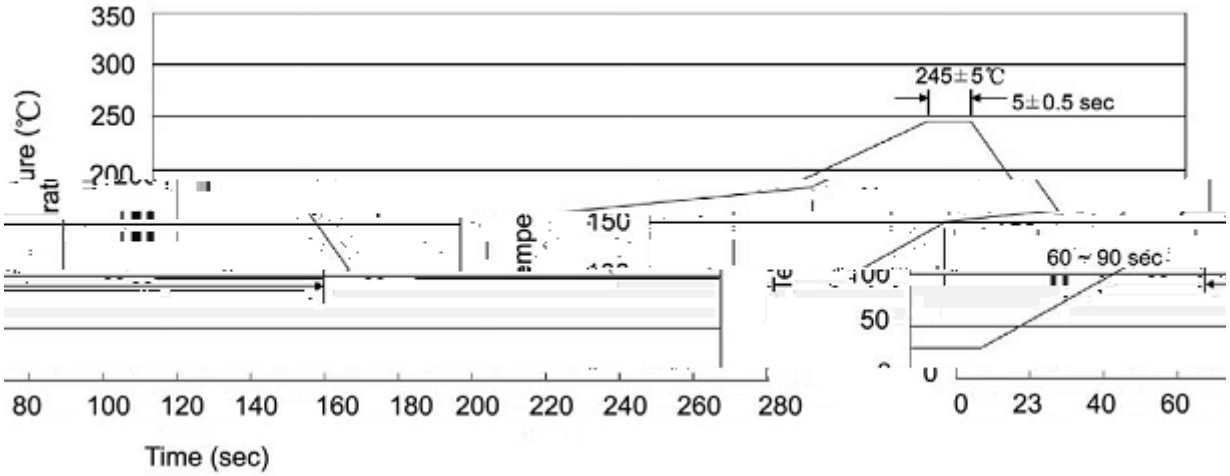
SOT-323

单位：mm





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Note:

1 25 150 60 90sec;

1.Preheating:25~150 , Time:60~90sec.

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